DISCRETE SEMICONDUCTORS



Product specification Supersedes data of December 1991 File under Discrete Semiconductors, SC01 1996 May 24





1996 May 24

Ultra fast low-loss controlled avalanche rectifiers

FEATURES

- · Glass passivated
- High maximum operating temperature

Philips Semiconductors

- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Shipped in 8 mm embossed tape
- Smallest surface mount rectifier outline.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage				
	BYD77A		_	50	V
	BYD77B		_	100	V
	BYD77C		_	150	V
	BYD77D		_	200	V
	BYD77E		_	250	V
	BYD77F		_	300	V
	BYD77G		_	400	V
V _R	continuous reverse voltage				
	BYD77A		_	50	V
	BYD77B		_	100	V
	BYD77C		-	150	V
	BYD77D		-	200	V
	BYD77E		-	250	V
	BYD77F		-	300	V
	BYD77G		-	400	V
I _{F(AV)}	average forward current	T_{tp} = 105 °C; see Figs 2 and 3;			
	BYD77A to D	averaged over any 20 ms period;	-	2.00	A
	BYD77E to G	see also Figs 10 and 11	-	1.85	A
I _{F(AV)}	average forward current	T _{amb} = 60 °C; PCB mounting (see			
	BYD77A to D	Fig.16); see Figs 4 and 5;	-	0.85	A
	BYD77E to G	averaged over any 20 ms period; see also Figs 10 and 11	-	0.80	А

DESCRIPTION

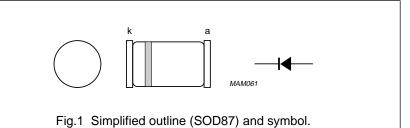
Cavity free cylindrical glass SOD87 package through Implotec^{TM(1)} technology. This package is

hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.



BYD77 series



BYD77 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{FRM}	repetitive peak forward current	T_{tp} = 105 °C; see Figs 6 and 7			
	BYD77A to D		_	15	A
	BYD77E to G		_	13	A
I _{FRM}	repetitive peak forward current	T _{amb} = 60 °C; see Figs 8 and 9			
	BYD77A to D		_	8.5	A
	BYD77E to G		_	8.0	A
I _{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave;	_	25	А
		$T_j = T_j \max_{max} prior to surge;$			
		$V_{R} = V_{RRMmax}$			
E _{RSM}	non-repetitive peak reverse	L = 120 mH; $T_j = 25 \text{ °C prior to}$	_	10	mJ
	avalanche energy	surge; inductive load switched off			
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature		-65	+175	°C

ELECTRICAL CHARACTERISTICS

 T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	$I_F = 1 A; T_j = T_{j max};$				
	BYD77A to D	see Figs 12 and 13	_	_	0.75	V
	BYD77E to G		_	-	0.83	V
V _F	forward voltage	I _F = 1 A;				
	BYD77A to D	see Figs 12 and 13	_	_	0.98	V
	BYD77E to G		_	-	1.05	V
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 0.1 mA				
	BYD77A		55	_	-	V
	BYD77B		110	_	-	V
	BYD77C		165	_	-	V
	BYD77D		220	-	-	V
	BYD77E		275	_	-	V
	BYD77F		330	_	-	V
	BYD77G		440	—	-	V
I _R	reverse current	V _R = V _{RRMmax} ; see Fig.14	_	_	1	μA
		$V_R = V_{RRMmax};$ T _j = 165 °C; see Fig.14	_	_	100	μA
t _{rr}	reverse recovery time	when switched from				
	BYD77A to D	$I_F = 0.5 \text{ A to } I_R = 1 \text{ A};$	_	_	25	ns
	BYD77E to G	measured at I _R = 0.25 A; see Fig.18	-	_	50	ns

BYD77 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C _d	diode capacitance	f = 1 MHz; V _R = 0 V;				
	BYD77A to D	see Fig.15	_	50	_	pF
	BYD77E to G		_	40	_	pF
dI _R dt	maximum slope of reverse recovery current	when switched from $I_F = 1 \text{ A to } V_R \ge 30 \text{ V}$				
	BYD77A to D	and $dI_F/dt = -1 A/\mu s$;	_	_	4	A/μs
	BYD77E to G	see Fig.17	_	_	5	A/μs

THERMAL CHARACTERISTICS

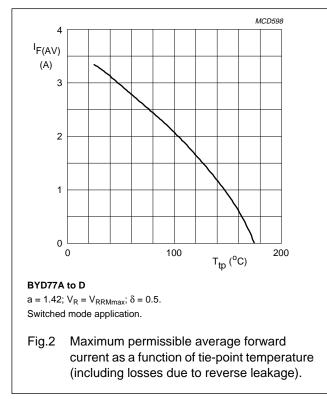
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point		30	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	150	K/W

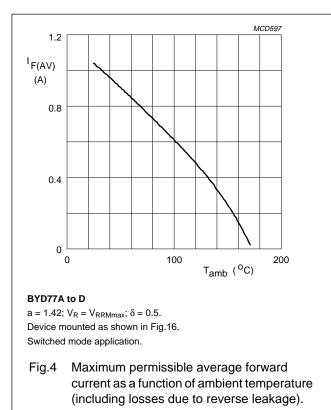
Note

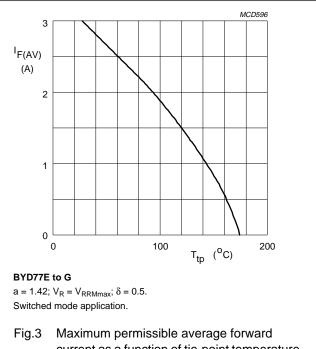
1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 μm, see Fig.16. For more information please refer to the *'General Part of Handbook SC01'*.

BYD77 series

GRAPHICAL DATA







current as a function of tie-point temperature (including losses due to reverse leakage).

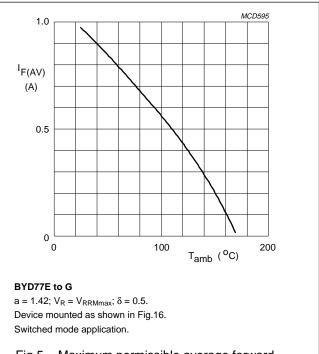
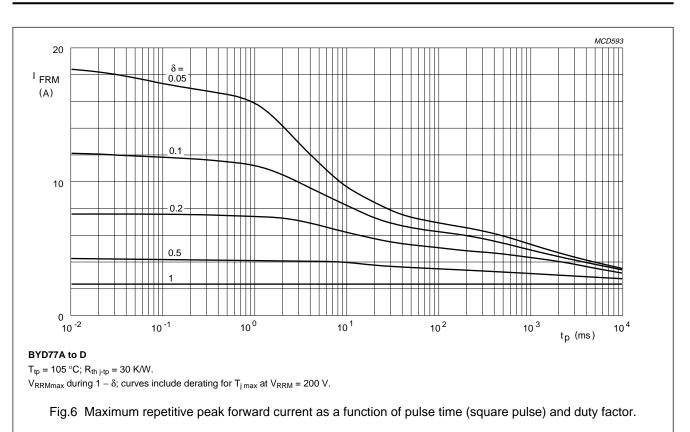


Fig.5 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

BYD77 series



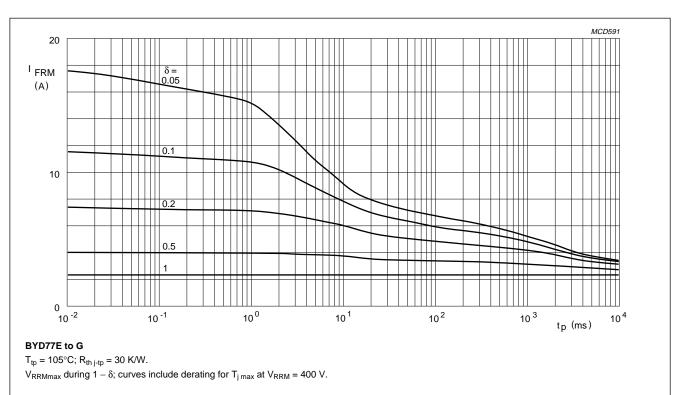
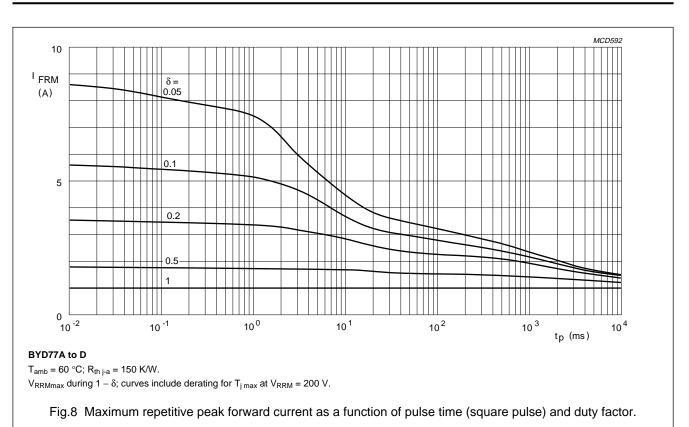


Fig.7 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

BYD77 series



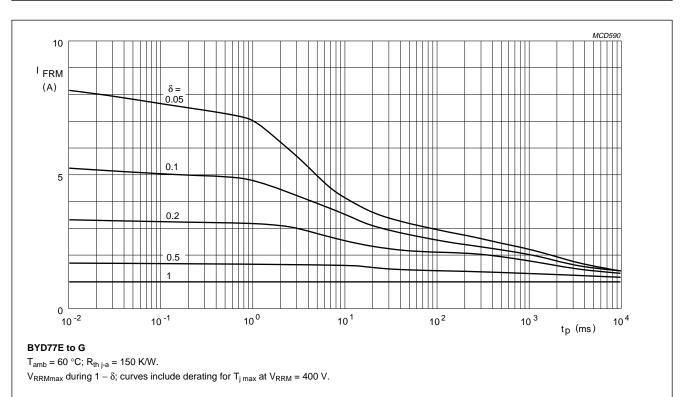
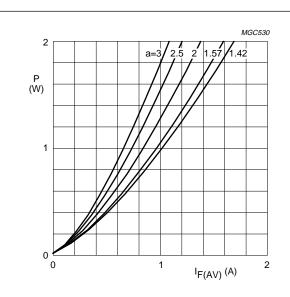


Fig.9 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

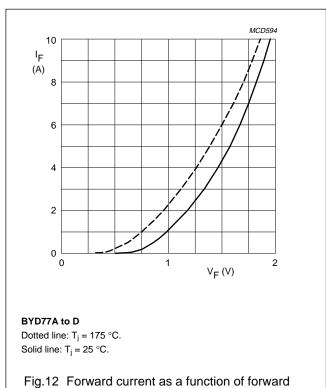
BYD77 series



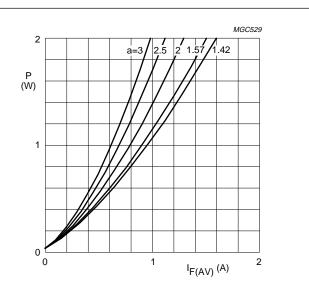
BYD77A to D

 $a = I_{F(RMS)}/I_{F(AV)}; V_{R} = V_{RRMmax}; \delta = 0.5.$

Fig.10 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



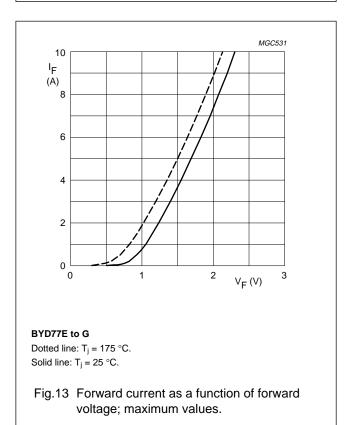
voltage; maximum values.



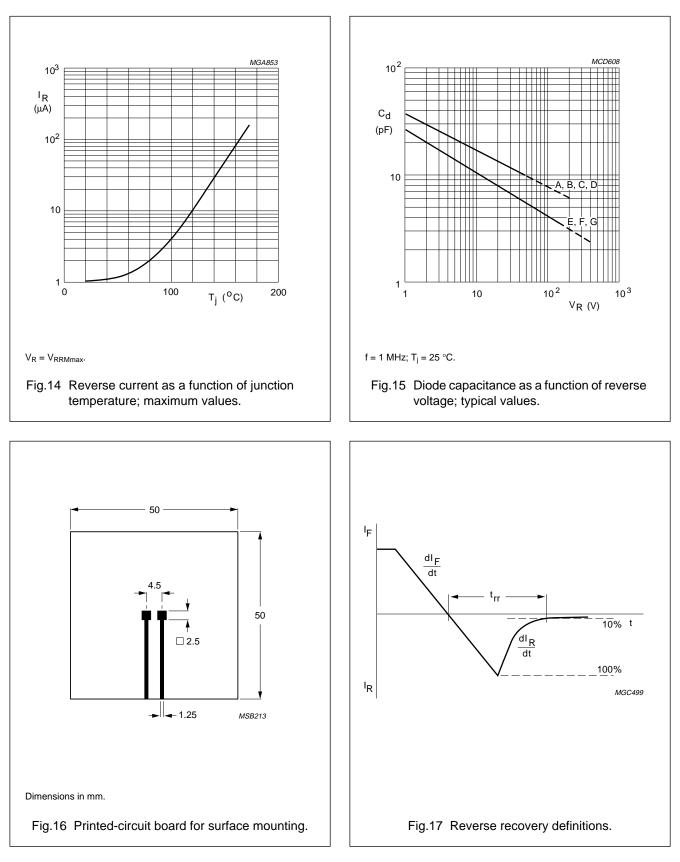
BYD77E to G

 $a = I_{F(RMS)}/I_{F(AV)}; V_R = V_{RRMmax}; \delta = 0.5.$

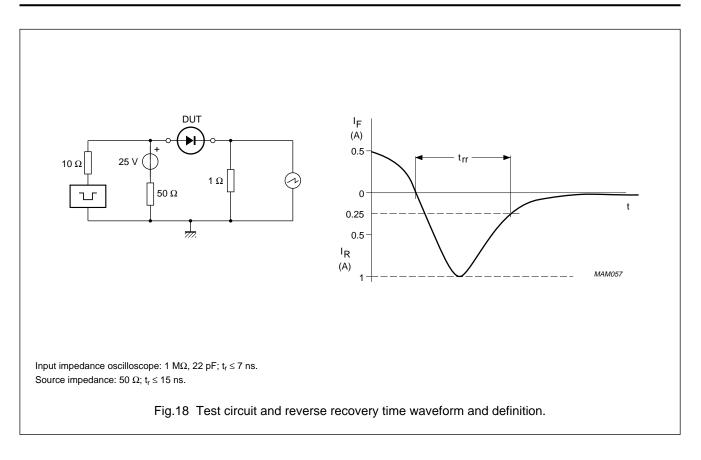
Fig.11 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



BYD77 series

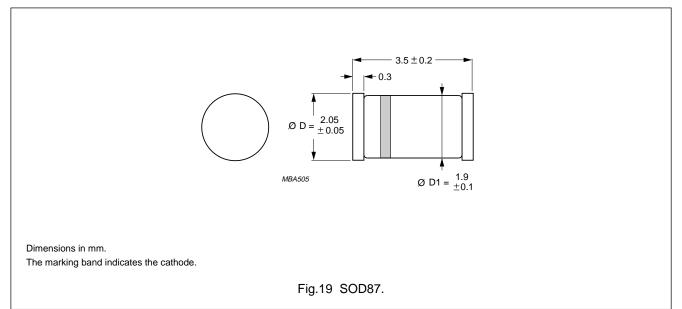


BYD77 series



BYD77 series

PACKAGE OUTLINE



DEFINITIONS

Data Sheet Status			
Objective specification This data sheet contains target or goal specifications for product development.			
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.		
Product specification	This data sheet contains final product specifications.		
Limiting values			
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.			
Application information			
Where application information is given, it is advisory and does not form part of the specification.			

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.